

Power Supply IC Series for TFT-LCD Panels

5V Input Multi-channel System Power Supply IC



BD8179MUV No.09035EBT04

Description

The BD8179MUV is a system power supply IC for TFT panels.

A 1-chip IC providing a total of three voltages required for TFT panels, i.e., source voltage, gate high-level, and gate low-level voltage, thus constructing a TFT panel power supply with minimal components required.

Features

- 1) Step Up DC/DC Converter.
- 2) Incorporates 18V, 3.0A N-channel FET
- 3) Linear-Regulator Controllers for VGON and VGOFF
- 4) 5 channel Operational Amplifiers/±150mA Output Short-Circuit Current 40V / µs Slew Rate
- 5) Switching Frequency: 1200 kHz.
- 6) Gate Shading Function Included.
- 7) Protection Circuits
- 8) Over Current Protection
- 9) Timer Latch Mode Short Current Protection.
- 10) Thermal Shut Down.
- 11) Under Voltage Protection.
- 12) Over Voltage Protection
- 13) VQFN032V5050 Package

Applications

Liquid crystal TV, PC monitor, and TFT-LCD panel

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limit	Unit
Power Supply Voltage	Vin	7	V
VMAIN Voltage	VMAIN	20	V
SUP Voltage	Vsup	20	V
DRVP Voltage	VDRVP	40	V
DRVN Voltage	Vdrvn	-30	V
SRC Voltage	Vsrc	40	V
CTL Voltage	VCTL	7	V
Junction Temperature	Tjmax	150	°C
Power Dissipation	Pd	4560	mW
Operating Temperature Range	Topr	-40~85	°C
Storage Temperature Range	Tstg	-55 ~ 150	°C

^{*} Reduced by 19.52 mW/°C over 25°C, when mounted on a glass epoxy board. (4-layer 74.2 mm \times 74.2 mm \times 1.6 mm).

Operating Condition

Darameter	Cymhol	Li	l lmi4		
Parameter	Symbol	Min.	Max.	Unit	
Power Supply Voltage	Vin	2.6	5.5	V	
VMAIN Voltage	VMAIN	8	18	V	
SUP Voltage	Vsup	-	18	V	
DRVP Voltage	VDRVP	-	38	V	
DRVN Voltage	Vdrvn	-	-20	V	
SRC Voltage	Vsrc	-	38	V	

● Electrical Characteristics (Unless otherwise specified, VIN = 3.3V; VSUP = 12 V; VGON = 25 V; VGOFF = -6V; Ta = 25°C) 1 DC/DC CONVERTER CONTROLLER BLOCK

I DC/DC CONVERTER CON	/DC CONVERTER CONTROLLER BLOCK Limit							
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions		
[ERROR AMPLIFIER BLOCK	K1							
FB Input Bias Current	IFB	-	0.1	_	μA			
Feed Back Voltage	VFB	1.221	1.233	1.245	V	Buffer, No load		
Comp Sink Current	loi	1	5	10	μA	VFB=1.5V VCOMP=0.5V		
Comp Source Current	loo	-10	-5	-1	<u>.</u> μΑ	VFB=1.0V VCOMP=0.5V		
[LX BLOCK]								
LX ON-Resistance	Ron	-	200	-	mΩ			
LX Leak Current	lleak	-	0	10	μA	VLX=18V		
MAX Duty Cycle	Dмах	-	90	-	%			
LX Current Limit	llx	2.5	-	-	Α			
[INTERNAL SOFT START BLOCK]								
Soft Start Delay Time	tss	-	3.25	-	ms			
2. GATE-ON LINEAR REGUI		ROLLER		1				
Parameter	Symbol	Limit		l lni4	Conditions			
r ai ai i i e lei	Syllibol	Min.	Тур.	Max.	Unit	Conditions		
FBP Voltage	VFBP	1.225	1.25	1.275	V			
FBP Input Bias Current	IFBP	-	0.1	-	μΑ			
DRVP Current Limit	IDRVP	1	5	10	mA			
3. GATE-OFF LINEAR REGU	JLATOR CONT	ROLLER						
Parameter	Symbol		Limit		Unit	Conditions		
- aramotor	3,5	Min.	Тур.	Max.		Conditions		
FBN Voltage	VFBN	0.235	0.25	0.265	V			
FBN Input Bias Current	IFBN	-	0.1	-	μA			
DRVN Current Limit	IDRVN	1	5	10	mA			
4. OPERATIONAL AMPLIFIE	RS							
Parameter	Symbol		Limit		Unit	Conditions		
	-	Min.	Тур.	Max.				
Input Offset Voltage	Voff	-	0	-	mV	Vpos1~5 = 6V		
Input Range	VRANGE	0		Vsup	V			
DRIVE Current	ldrv	50	-	-	mA			
Slew Rate	SR	-	40	-	V/us			
5. GATE SHADING CONTRO	DLLER BLOCK							
Parameter	Symbol		Limit		Unit	Conditions		
DEL OL LD C		Min.	Typ.	Max.				
DEL Start Period	tdd	-	15	-	ms			
DEL Source Current	Idls	-8	-5	-2	μA			
DEL Threshold Voltage	Vdls	1.2	1.25	1.3	V			
CTL Input Low Voltage	VctII	-	-	VIN x 0.3	V			
CTL Input High Voltage	Vchlh	VIN x 0.7		-	V			
CTL Input Current	Ictl	8	16.5	25	μA	VCTL=3.3V		
SRC ON Resistance	Ronsrc	-	5	-	Ω			
DRN ON Resistance	Rondry	-	30	-	Ω			

OThis product is not designed for protection against radioactive rays.

● Electrical Characteristics (Unless otherwise specified, VIN = 3.3V; VSUP = 12 V; VGON = 25 V; VGOFF = -6V; Ta = 25°C) 6. WHOLE DEVICE

O. WHOLL DEVICE							
Parameter	Symbol	Limit			Unit	Conditions	
Farameter		Min.	Тур.	Max.	Offic	Conditions	
[REFERENCE BLOCK]							
Reference Voltage	VREF	1.231	1.25	1.269	V		
[OSCILLATION BLOCK]							
Oscillation Frequency	Fosc	1020	1200	1380	kHz		
[VIN UNDER VOLTAGE LOCK OUT BLOCK]							
Detect Voltage	Vuvlo	2.25	2.4	2.55	V		
[SUP OVER VOLTAGE LOCK (OUT BLOCK]					
Detect Voltage	Vovp	18	19	20	V		
SHORT CURRENT PROTECT	ION BLOCK	[]					
Fault Delay Time	Tscp	-	150	-	ms		
[DETECTOR BLOCK]							
VFB OFF Threshold Voltage	Vthfb	0.9	1.0	1.1	V		
VFBP OFF Threshold Voltage	Vthfbp	0.9	1.0	1.1	V		
VFBN OFF Threshold Voltage	Vthfpn	0.4	0.5	0.6	V		

OThis product is not designed for protection against radio active rays.

● Reference Data (Unless otherwise specified, Ta = 25°C, VIN=5V)

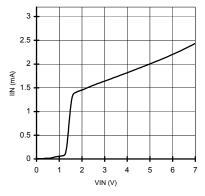


Fig.1 Supply Current (No switching)

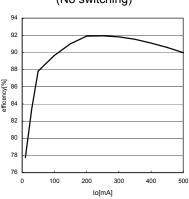


Fig.4 Efficiency vs Output Current (VMAIN)

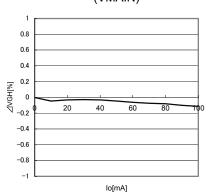


Fig.7 Gate-ON Voltage Load Regulation

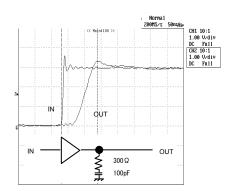


Fig.10 AMP Slew Rate (Rise)

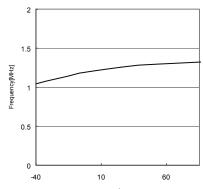


Fig.2 Switching Frequency vs Temperature

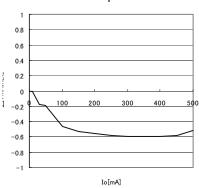


Fig.5 VMAIN Voltage Load Regulation

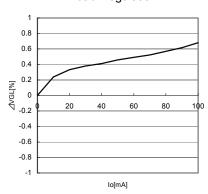


Fig.8 Gate-OFF Voltage Load Regulation

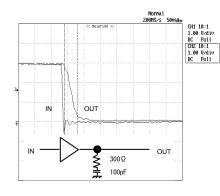


Fig.11 AMP Slew Rate (Fall)

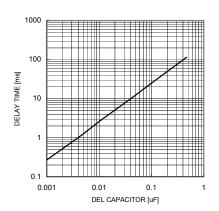


Fig.3 Delay Time vs Capacitor

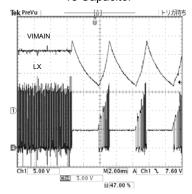


Fig.6 Over Voltage Protect waveform

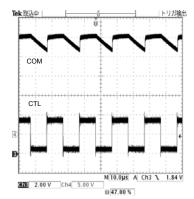


Fig.9 Gate Shading Output waveform

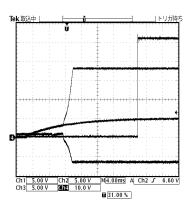
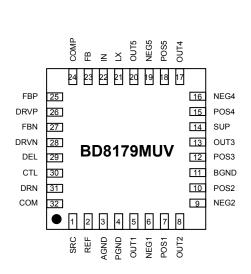
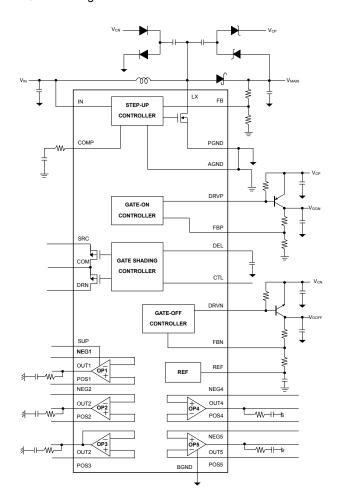


Fig.12 Start Up Sequence waveform

Pin Assignments Diagram



●Block Diagram



Pin Assignments

PIN NO.	Pin Name	Function		Pin Name	Function
1	SRC	Highside Input for Gate Shading switch	17	OUT4	Operational Amplifier 4 Output
2	REF	Reference for VGOFF	18	POS5	Operational Amplifier 5 Noninverting Input
3	AGND	Ground	19	NEG5	Operational Amplifier 5 Inverting Input
4	PGND	Power Ground	20	OUT5	Operational Amplifier 5 Output
5	OUT1	Operational Amplifier 1 Output	21	LX	Nch Power MOS FET Drain and Switching Node
6	NEG1	Operational Amplifier 1 Inverting Input	22	IN	Power Supply voltage Input
7	POS1	Operational Amplifier 1 Noninverting Input	23	FB	Feedback Input for step up DC/DC
8	OUT2	Operational Amplifier 2 Output	24	COMP	Error Amplifier Compensation Point for step up DC/DC
9	NEG2	Operational Amplifier 2 Inverting Input	25	FBP	Feedback Input for Gate-ON Linear-Regulator
10	POS2	Operational Amplifier 2 Noninverting Input	26	DRVP	Gate-ON Linear-Regulator Base Drive
11	BGND	Ground	27	FBN	Feedback Input for Gate-OFF Linear-Regulator
12	POS3	Operational Amplifier 3 Noninverting Input	28	DRVN	Gate-OFF Linear-Regulator Base Drive
13	OUT3	Operational Amplifier 3 Output	29	DEL	Delay Input for Gate Shading
14	SUP	Power Supply voltage Input for operational Amplifier	30	CTL	Switch Control Input for Gate Shading
15	POS4	Operational Amplifier 4 Noninverting Input	31	DRN	Lowside Input for Gate Shading switch
16	NEG4	Operational Amplifier 4 Inverting Input	32	COM	Gate Shading Output

●Block Function

Step-up Controller

A controller circuit for DC/DC boosting.

The switching duty is controlled so that the feedback voltage FB is set to 1.233 V (typ.).

A soft start operates at the time of starting.

Gate-on Controller

A controller circuit for the positive-side charge pump.

The liner regulator controls so that the feedback voltage FBP will be set to 1.25 V (typ.).

Gate-off Controller

A controller circuit for the negative-side charge pump.

The liner regulator controls so that the feedback voltage FBN will be set to 0.25 V (Typ.).

· Gate Shading Controller

A controller circuit for MOS FET Switch

The COM switching synchronize with CTL input.

Start-up Controller

A control circuit for the starting sequence.

Controls to start in order of VCC →VMAIN →VGOFF/VGON→VCOM

• RFF

A block that generates internal reference voltage. 1.25V (Typ.) is output.

TSD/UVLO/OVP

Thermal shutdown/Under-voltage lockout protection/circuit blocks.

The thermal shutdown circuit is shut down at an IC internal temperature of 175°C and reactivate at 160°C.

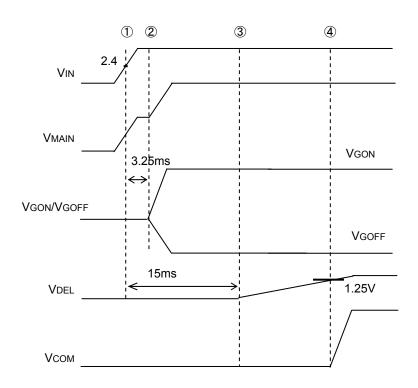
The under-voltage lockout protection circuit shuts down the IC when the VIN is 2.4 V (typ.) or below.

The over-voltage lockout protection circuit shuts down the IC when the SUP is 19.0 V (typ.) or over.

• OP1~OP5

Operational amplifier block

Starting sequence



- **1)UVLO** released when VIN voltage reaches 2.4V
- 2Step up DCDC converter starts switching, and VGON and VGOFF starts.
- 3VDEL starts.
- **4**Vcoм ON when VDEL reaches 1.25V

BD8179MUV Technical Note

●Under Voltage Lock Out (UVLO)

The UVLO circuit compares the input voltage at IN with the UVLO threshold (2.4V rising, 2.2V falling, typ) to ensure the input voltage is high enough for reliable operation.

The 200mV (typ) hysteresis prevents supply transients from causing a restart. Once the input voltage exceeds the UVLO rising threshold, startup begins. When the input voltage falls below the UVLO falling threshold, the controller turns off the main step-up regulator, turns off the linear-regulator outputs, and disables the Gate Shading controller.

●Thermal Shut Down (TSD)

The TSD prevents excessive power dissipation from overheating the BD8179MUV. When the junction temperature exceeds Tj=175°C(Typ), a thermal sensor immediately activates. The fault protection, which shuts down all outputs except the reference, allowing the device to cool down. Once the device cools down by approximately 15°C reactivate the device.

Over Voltage Protection (OVP)

The Step up DC/DC converter has OVP circuit.

The OVP circuit compares the input Voltage at SUP with the OVP threshold (19V rising, 18.5V falling, Typ) to protect the step up DC/DC output exceed the absolute maximum voltage. Once the SUP Voltage exceeds the OVP rising threshold, turn off the main Step-up regulator.

Then, the SUP Voltage falls bellow the OVP falling threshold, reactivate the main Step-Up regulator.

Over Current Protection (OCP)

The Step-Up DC/DC converter, linear-regulator and Operational Amplifier have OCP circuit respectively.

The OCP circuit restricts to load current, when an OCP activated, one's own output only restricted.

However, if the output continue to overload, the device is possible to activate thermal shutdown or short current protection.

●Timer Latch Mode Short Current Protection (SCP)

BD8179MUV has SCP circuit feature to prevent the large current flowing when the output is shorted to GND.

This function is monitoring VMAIN, VGON, and VGOFF Voltage and starts the timer when at least one of the outputs operating properly (when the output voltage was lower than expected).

After 150ms (Typ.) of this abnormal state, the device will shutdown the all outputs and latch the state.

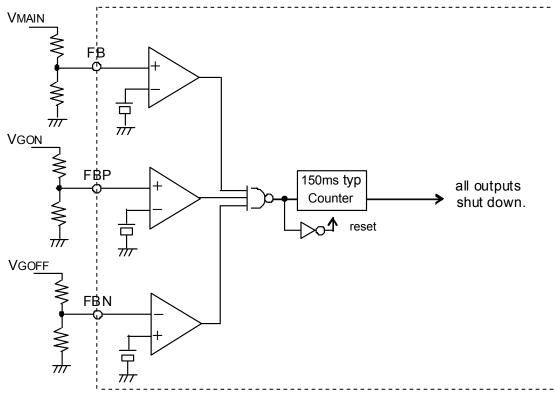


Fig.13 SCP Block Diagram

Selecting Application Components

(1) Setting the Output L Constant

The coil to use for output is decided by the rating current ILR and input current maximum value IINMAX of the coil.

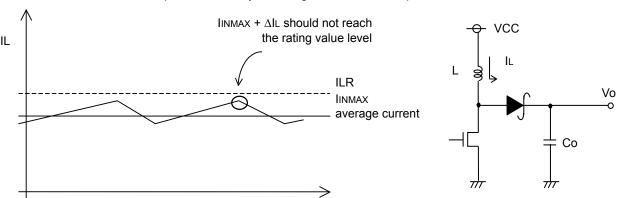


Fig.14 Coil Current Waveform

Fig. 15 Output Application Circuit Diagram

Adjust so that Innmax $+\Delta IL$ does not reach the rating current value ILR. At this time, ΔIL can be obtained by the following equation.

$$\Delta IL = \frac{1}{L} \frac{Vcc}{\times} \frac{Vo-Vcc}{Vcc} \times \frac{1}{f}$$
 [A] Here, f is the switching frequency.

Set with sufficient margin because the coil value may have the dispersion of $\pm 30\%$. If the coil current exceeds the rating current ILR of the coil, it may damage the IC internal element.

BD8179MUV uses the current mode DC/DC converter control and has the optimized design at the coil value. A coil inductance (L) of $4.7 \mu H$ to $15 \mu H$ is recommended from viewpoints of electric power efficiency, response, and stability.

(2) Output Capacity Settings

For the capacitor to use for the output, select the capacitor which has the larger value in the ripple voltage VPP allowance value and the drop voltage allowance value at the time of sudden load change. Output ripple voltage is decided by the following equation.

$$\triangle VPP = ILMAX \times RESR + \frac{1}{fCo} \times \frac{Vcc}{Vo} \times (ILMAX - \frac{\triangle IL}{2})$$
 [V] Here, f is the switching frequency.

Perform setting so that the voltage is within the allowable ripple voltage range. For the drop voltage during sudden load change; VDR, please perform the rough calculation by the following equation.

$$V_{DR} = \frac{\Delta I}{C_0} \times 10 \text{ us}$$
 [V]

However, 10 μ s is the rough calculation value of the DC/DC response speed. Please set the capacitance considering the sufficient margin so that these two values are within the standard value range.

(3) Selecting the Input Capacitor

Since the peak current flows between the input and output at the DC/DC converter, a capacitor is required to install at the input side. For the reason, the low ESR capacitor is recommended as an input capacitor which has the value more than $10 \, \mu F$ and less than $100 \, m\Omega$. If a capacitor out of this range is selected, the excessive ripple voltage is superposed on the input voltage, accordingly it may cause the malfunction of IC.

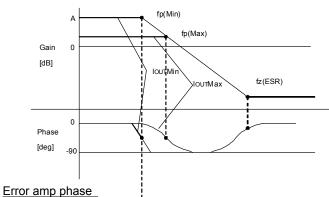
However these conditions may vary according to the load current, input voltage, output voltage, inductance and switching frequency. Be sure to perform the margin check using the actual product.

Technical Note BD8179MUV

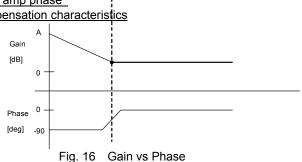
(4) Setting Rc, Cc of the Phase Compensation Circuit

In the current mode control, since the coil current is controlled, a pole (phase lag) made by the CR filter composed of the output capacitor and load resistor will be created in the low frequency range, and a zero (phase lead) by the output capacitor and ESR of capacitor will be created in the high frequency range. In this case, to cancel the pole of the power amplifier, it is easy to compensate by adding the zero point with Cc and Rc to the output from the error amp as shown in the illustration.

Open loop gain characteristics



compensation characteristics



$$\mathsf{Fp} = \frac{1}{2 \ \pi \times \mathsf{Ro} \times \mathsf{Co}} \quad [\mathsf{Hz}]$$

$$fz(ESR) = \frac{1}{2\pi \times ESR \times CO}$$
 [Hz]

Pole at the power amplification stage

When the output current reduces, the load resistance Ro increases and the pole frequency lowers.

$$fp(Min) = \frac{1}{2 \pi \times ROMax \times CO} [Hz] \leftarrow at light load$$

$$fz(Max) = \frac{1}{2 \pi \times ROMin \times CO} [Hz] \leftarrow at heavy load$$

Zero at the power amplification stage

When the output capacitor is set larger, the pole frequency lowers but the zero frequency will not change. (This is because the capacitor ESR becomes 1/2 when the capacitor becomes 2 times.)

$$fp(Amp.) = \frac{1}{2 \pi \times Rc \times Cc} [Hz]$$

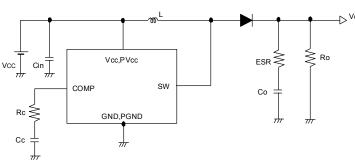


Fig. 17 Application Circuit Diagram

It is possible to realize the stable feedback loop by canceling the pole fp(Min.), which is created by the output capacitor and load resistor, with CR zero compensation of the error amp as shown below.

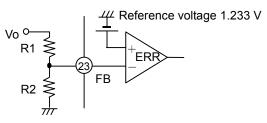
fz(Amp.) = fp(Min.)

$$\frac{1}{2 \pi \times Rc \times Cc} - \frac{1}{2 \pi \times Romax \times C} [Hz]$$

(5) Design of the Feedback Resistor Constant

Refer to the following equation to set the feedback resistor. As the setting range, $10 \text{ k}\Omega$ to $330 \text{ k}\Omega$ is recommended. If the resistor is set lower than a $10 \text{ k}\Omega$, it causes the reduction of power efficiency. If it is set more than $330 \text{ k}\Omega$, the offset voltage becomes larger by the input bias current $0.4 \mu A(\text{Typ.})$ in the internal error amplifier.

$$V_{MAIN} = \frac{R1 + R2}{R2} \times 1.233$$
 [V]



(6) Positive-side Charge Pump Settings

BD8179MUV incorporates a charge pump controller, thus making it possible to generate stable gate voltage. The output voltage is determined by the following formula. As the setting range, $10~k\Omega$ to $330~k\Omega$ is recommended. If the resistor is set lower than a $10k\Omega$, it causes the reduction of power efficiency. If it is set more than $330~k\Omega$, the offset voltage becomes larger by the input bias current $0.4~\mu$ A (Typ.) in the internal error amp.

$$V_{GON} = \frac{R3 + R4}{R4} \times 1.25 \quad [V]$$

$$1000 \text{ pF to } 4700 \text{ pF}$$

$$R8 = \frac{1.25 \text{ V}}{R4} \times 1.25 \quad [V]$$

In order to prevent output voltage overshooting, add capacitor C3 in parallel with R3. The recommended capacitance is 1000 pF to 4700 pF. If a capacitor outside this range is inserted, the output voltage may oscillate.

By connecting capacitance to the DEL, a rising delay time can be set for the positive-side charge pump.

The delay time is determined by the following formula.

• Delay time of charge pump block t DELAY

t DELAY = (CDEL
$$\times$$
 1.25)/5 μ A [s]

Where, CDEL is the external capacitance.

(7) Negative-side Charge Pump Settings

BD8179MUV incorporates a charge pump controller for negative voltage, thus making it possible to generate stable gate voltage. The output voltage is determined by the following formula. As the setting range, $10 \text{ k}\Omega$ to $330 \text{ k}\Omega$ is recommended. If the resistor is set lower than a $10 \text{ k}\Omega$, it causes the reduction of power efficiency. If it is set more than $330 \text{ k}\Omega$, the offset voltage becomes larger by the input bias current $0.4 \text{ }\mu\text{A}$ (Typ.) in the internal error amp.

$$V_{GOFF} = -\frac{R5}{R6} \times 1.0 + 0.25 \text{ V}$$
 [V] 1000 pF to 4700 pF R6 R6 RF T1.25 V

The delay time is internally fixed at 200 us.

In order to prevent output voltage overshooting, insert capacitor C5 in parallel with R5. The recommended capacitance is 1000 pF to 4700 pF. If a capacitor outside this range is inserted, the output voltage may oscillate.

BD8179MUV Technical Note

Notes for use

1) Absolute maximum ratings

Use of the IC in excess of absolute maximum ratings such as the applied voltage or operating temperature range may result in IC damage. Assumptions should not be made regarding the state of the IC (short mode or open mode) when such damage is suffered. A physical safety measure such as a fuse should be implemented when use of the IC in a special mode where the absolute maximum ratings may be exceeded is anticipated.

2) GND potential

Ensure a minimum GND pin potential in all operating conditions.

3) Setting of heat

Use a thermal design that allows for a sufficient margin in light of the power dissipation (Pd) in actual operating conditions.

4) Pin short and mistake fitting

Use caution when orienting and positioning the IC for mounting on printed circuit boards. Improper mounting may result in damage to the IC. Shorts between output pins or between output pins and the power supply and GND pins caused by the presence of a foreign object may result in damage to the IC.

5) Actions in strong magnetic field

Use caution when using the IC in the presence of a strong magnetic field as doing so may cause the IC to malfunction.

6) Testing on application boards

When testing the IC on an application board, connecting a capacitor to a pin with low impedance subjects the IC to stress. Always discharge capacitors after each process or step. Ground the IC during assembly steps as an antistatic measure, and use similar caution when transporting or storing the IC. Always turn the IC's power supply off before connecting it to or removing it from a jig or fixture during the inspection process.

7) Ground wiring patterns

When using both small signal and large current GND patterns, it is recommended to isolate the two ground patterns, placing a single ground point at the application's reference point so that the pattern wiring resistance and voltage variations caused by large currents do not cause variations in the small signal ground voltage. Be careful not to change the GND wiring patterns of any external components.

8) This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P/N junctions are formed at the intersection of these P layers with the N layers of other elements to create a variety of parasitic elements. For example, when the resistors and transistors are connected to the pins as shown in Fig. 18, a parasitic diode or a transistor operates by inversing the pin voltage and GND voltage.

The formation of parasitic elements as a result of the relationships of the potentials of different pins is an inevitable result of the IC's architecture. The operation of parasitic elements can cause interference with circuit operation as well as IC malfunction and damage. For these reasons, it is necessary to use caution so that the IC is not used in a way that will trigger the operation of parasitic elements, such as the application of voltages lower than the GND (P board) voltage to input and output pins.

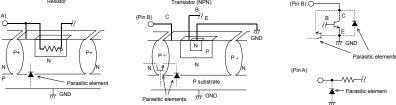


Fig.18 Example of a Simple Monolithic IC Architecture

9) Overcurrent protection circuits

An overcurrent protection circuit designed according to the output current is incorporated for the prevention of IC destruction that may result in the event of load shorting. This protection circuit is effective in preventing damage due to sudden and unexpected accidents. However, the IC should not be used in applications characterized by the continuous operation or transitioning of the protection circuits. At the time of thermal designing, keep in mind that the current capability has negative characteristics to temperatures.

10) Thermal shutdown circuit

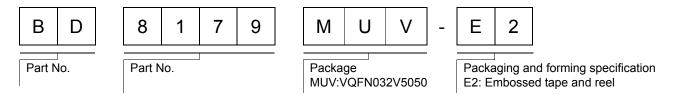
This IC incorporates a built-in thermal shutdown circuit for the protection from thermal destruction. The IC should be used within the specified power dissipation range. However, in the event that the IC continues to be operated in excess of its power dissipation limits, the attendant rise in the chip's temperature Tj will trigger the thermal shutdown circuit to turn off all output power elements. The circuit automatically resets once the chip's temperature Tj drops.

Operation of the thermal shutdown circuit presumes that the IC's absolute maximum ratings have been exceeded. Application designs should never make use of the thermal shutdown circuit.

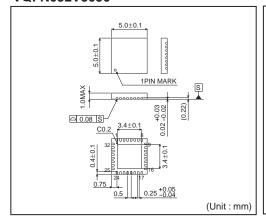
11) Testing on application boards

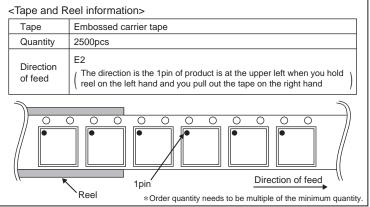
At the time of inspection of the installation boards, when the capacitor is connected to the pin with low impedance, be sure to discharge electricity per process because it may load stresses to the IC. Always turn the IC's power supply off before connecting it to or removing it from a jig or fixture during the inspection process. Ground the IC during assembly steps as an antistatic measure, and use similar caution when transporting or storing the IC.

Ordering part number



VQFN032V5050





Notes

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